0	10

Symbol	Parameter	Values	Unit
CES	Collector-emitter voltage	650	V
GES	Gate-emitter voltage	±20	V
C	Continuous collector current (C=25)	20	A
	Continuous collector current (C=100)	10	A
CM	Pulsed collector current, p limited by vjmax	40	A
F	Diode continuous forward current (C=100)	10	A
FM	Diode maximum current, p limited by vjmax	40	A
sc	Short circuit withstand time	10	µs
tot	Power dissipation (C=25)	136	W
	Power dissipation (C=100 ůĊH Td(@ŽHI ƒE) P		

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
$_{CES}$	Collector-emitter breakdown voltage	$_{GE}$=0V, $_{C}$=250μA	650	-	-	V
$_{CES}$	Collector-emitter leakage current	$_{CE}$=650V, $_{GE}$=0V	-	-	50	μA

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ		

Electrical characteristics of Diode ($_{vj}$=25 unless otherwise specified)

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
$_{F}$	Diode forward voltage	$_{F}$=10A	-	1.4	-	V
		$_{F}$=10A, $_{vj}$=175	-	1.2	-	V
$_{rr}$	Diode reverse recovery time	$_{R}$=400V $_{F}$=10A d $_{F}$/d =-750A/μs	-	57	-	ns
$_{rrm}$	Diode peak reverse recovery current		-	12	-	A
$_{rr}$	Diode reverse recovery charge		-	411	-	nC
$_{rr}$	Diode reverse recovery time	$_{R}$=400V $_{F}$=10A d $_{F}$/d =-750A/μs $_{vj}$=175	-	124	-	ns
$_{rrm}$	Diode peak reverse recovery current		-	13	-	A
$_{rr}$	Diode reverse recovery charge		-	737	-	nC

p performance characteristics

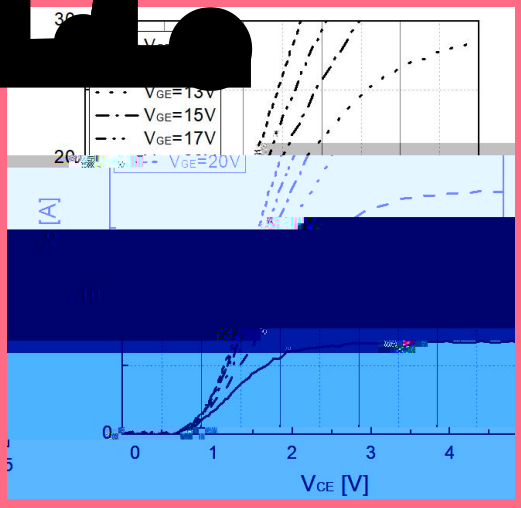


Fig 1. Typical output characteristic (vj=25)

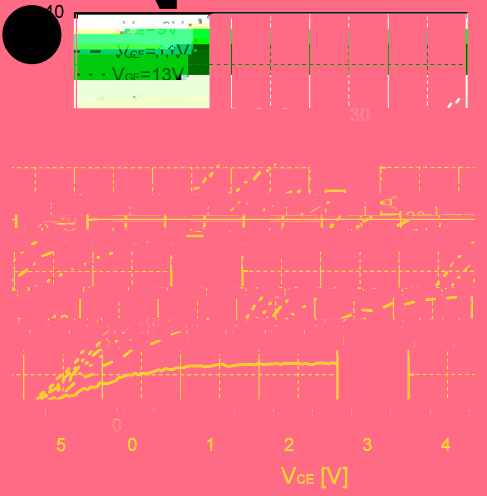


Fig 2. Typical output characteristic(vj=175)

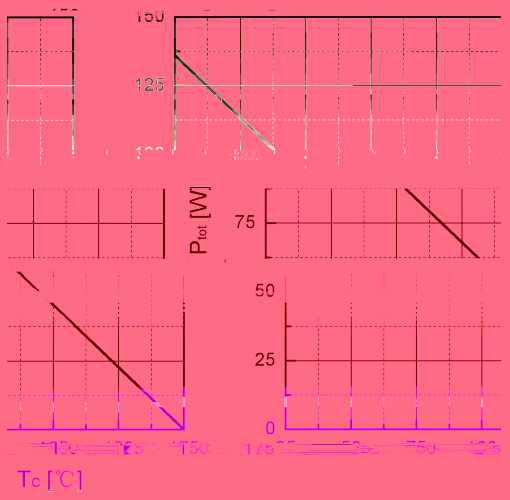
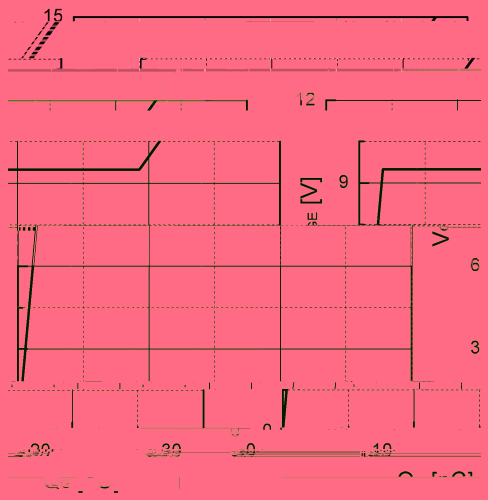


Fig 3. Power i ricw א ע Î



Typical performance characteristics

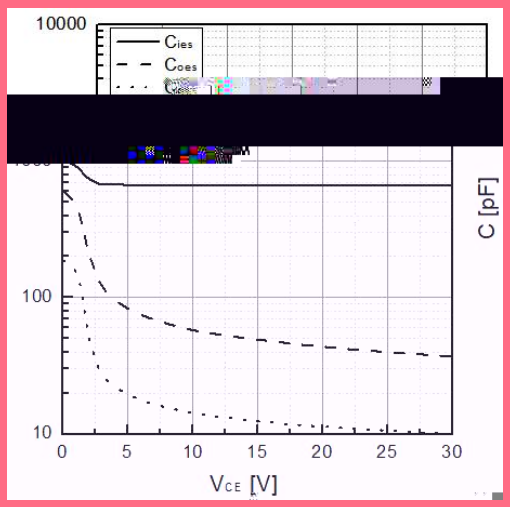


Fig 13. Typical capacitance as a function of $_{CE}$ (f=1Mhz, $_{GE}$=0V)

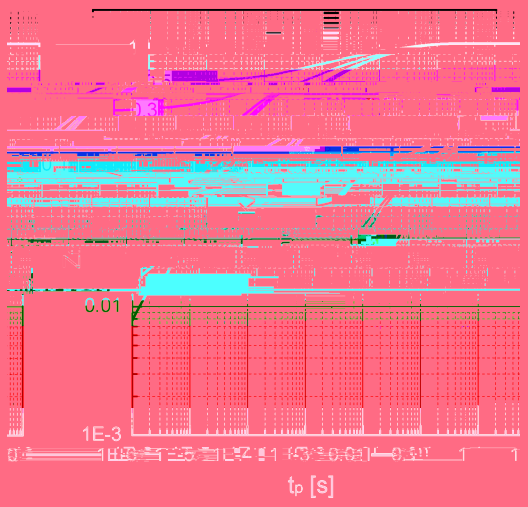
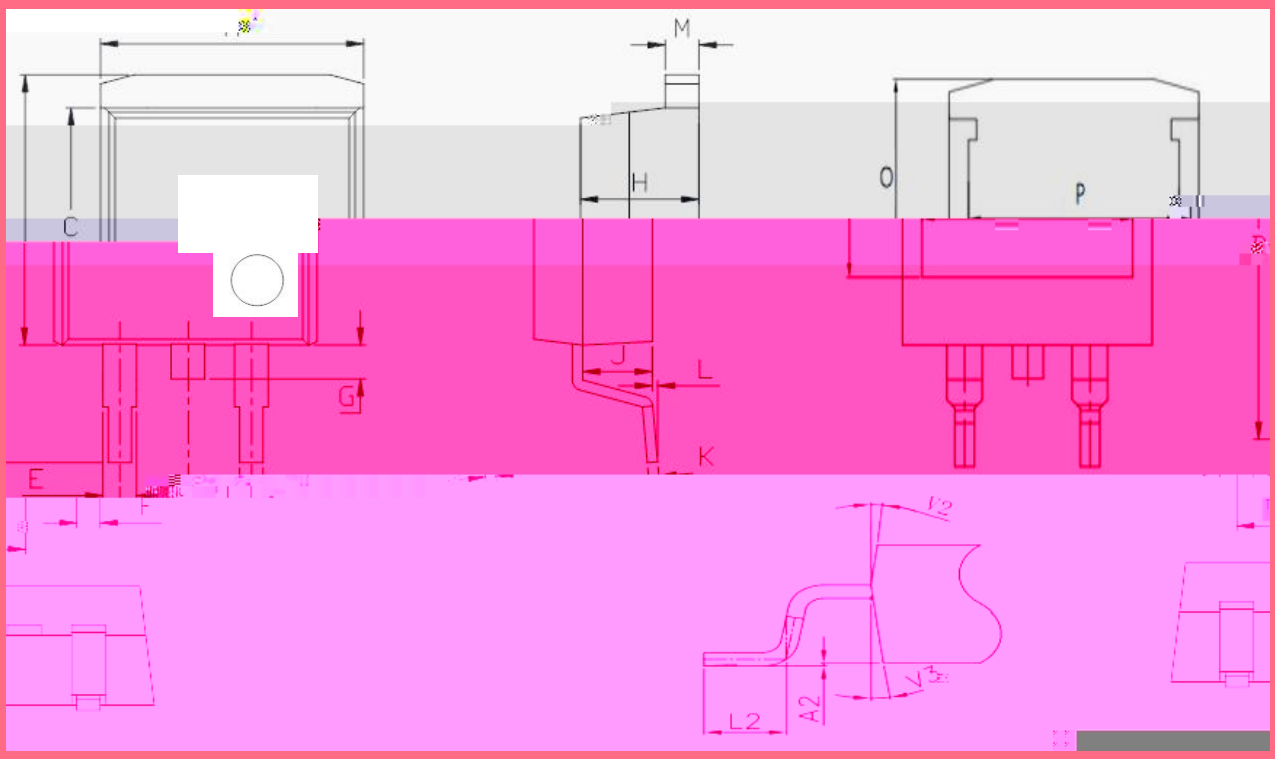


Fig 14. Transient thermal impedance of IGBT

Package dimension

TO-263



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90	-	10.20	0.390	-	0.402
B	14.70	-	15.80	0.579	-	0.622
C	8.8	-	9.4	0.346	-	0.370
D	-	2.54	-	-	0.100	-
E	1.37	-	1.57	0.054	-	0.062
F	0.75	-	0.85	0.029	-	0.033
G	-	-	1.75	-	-	0.069
H	4.30	-	4.70	0.169	-	0.185
J	2.30	-	2.70	0.091	-	0.106
K	0.38	-	0.55	0.015	-	0.022
L	0	0.15	0.25	0	0.006	0.010
M	1.25	-	1.35	0.049	-	0.053
O	7.4	7.65	7.9	0.291	0.301	0.311
P	8.3	8.6	8.9	0.327	0.339	0.350
L2	2.20	2.35	2.50	0.087	0.093	0.098

Revision history

Date	Revision	Changes
2023-12-23	Rev 1.0	Release of the datasheet
2025-02-06	Rev 1.1	Update
2025-04-08	Rev 1.2	Character Update
2026-03-12	Rev 1.3	Update POD
2026-06-23	Rev 1.4	Update thermal

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